

Kin M Yu

List of Publications by Citations

Source: <https://exaly.com/author-pdf/7827591/kin-m-yu-publications-by-citations.pdf>

Version: 2024-04-24

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

500
papers

15,865
citations

59
h-index

110
g-index

538
ext. papers

17,113
ext. citations

3.5
avg, IF

6.03
L-index

#	Paper	IF	Citations
500	Unusual properties of the fundamental band gap of InN. <i>Applied Physics Letters</i> , 2002 , 80, 3967-3969	3.4	1254
499	Superior radiation resistance of In _{1-x} Ga _x N alloys: Full-solar-spectrum photovoltaic material system. <i>Journal of Applied Physics</i> , 2003 , 94, 6477-6482	2.5	503
498	Small band gap bowing in In _{1-x} Ga _x N alloys. <i>Applied Physics Letters</i> , 2002 , 80, 4741-4743	3.4	498
497	Effect of the location of Mn sites in ferromagnetic Ga _{1-x} Mn _x As on its Curie temperature. <i>Physical Review B</i> , 2002 , 65,	3.3	461
496	Observation of crystalline C ₃ N ₄ . <i>Physical Review B</i> , 1994 , 49, 5034-5037	3.3	458
495	Effects of the narrow band gap on the properties of InN. <i>Physical Review B</i> , 2002 , 66,	3.3	346
494	Temperature dependence of the fundamental band gap of InN. <i>Journal of Applied Physics</i> , 2003 , 94, 4457-4460	3.3	337
493	Valence-band anticrossing in mismatched III-V semiconductor alloys. <i>Physical Review B</i> , 2007 , 75,	3.3	310
492	Valence band anticrossing in GaBi _x As _{1-x} . <i>Applied Physics Letters</i> , 2007 , 91, 051909	3.4	262
491	Nature of room-temperature photoluminescence in ZnO. <i>Applied Physics Letters</i> , 2005 , 86, 191911	3.4	237
490	Engineering the electronic band structure for multiband solar cells. <i>Physical Review Letters</i> , 2011 , 106, 028701	7.4	225
489	Diluted II-VI oxide semiconductors with multiple band gaps. <i>Physical Review Letters</i> , 2003 , 91, 246403	7.4	219
488	Large, nitrogen-induced increase of the electron effective mass in In _y Ga _{1-y} N _x As _{1-x} . <i>Applied Physics Letters</i> , 2000 , 76, 2409-2411	3.4	212
487	Structure and electronic properties of InN and In-rich group III-nitride alloys. <i>Journal Physics D: Applied Physics</i> , 2006 , 39, R83-R99	3	211
486	Nature of the fundamental band gap in GaN _x P _{1-x} alloys. <i>Applied Physics Letters</i> , 2000 , 76, 3251-3253	3.4	211
485	Evidence for p-type doping of InN. <i>Physical Review Letters</i> , 2006 , 96, 125505	7.4	176
484	Fermi-level stabilization energy in group III nitrides. <i>Physical Review B</i> , 2005 , 71,	3.3	172

483	Mechanistic insights into chemical and photochemical transformations of bismuth vanadate photoanodes. <i>Nature Communications</i> , 2016 , 7, 12012	17.4	169
482	Interaction of localized electronic states with the conduction band: band anticrossing in II-VI semiconductor ternaries. <i>Physical Review Letters</i> , 2000 , 85, 1552-5	7.4	162
481	Controlling the Curie temperature in (Ga,Mn)As through location of the Fermi level within the impurity band. <i>Nature Materials</i> , 2012 , 11, 444-9	27	148
480	Optical properties and electronic structure of InN and In-rich group III-nitride alloys. <i>Journal of Crystal Growth</i> , 2004 , 269, 119-127	1.6	145
479	Ni, Pd, and Pt on GaAs: A comparative study of interfacial structures, compositions, and reacted film morphologies. <i>Journal of Materials Research</i> , 1987 , 2, 262-275	2.5	137
478	Effect of vacuum arc deposition parameters on the properties of amorphous carbon thin films. <i>Surface and Coatings Technology</i> , 1994 , 68-69, 388-393	4.4	121
477	Novel metal ion surface modification technique. <i>Applied Physics Letters</i> , 1991 , 58, 1392-1394	3.4	119
476	Breakdown of crystallinity in low-temperature-grown GaAs layers. <i>Applied Physics Letters</i> , 1991 , 58, 2153-2155	3.4	113
475	Multiband GaNAsP quaternary alloys. <i>Applied Physics Letters</i> , 2006 , 88, 092110	3.4	112
474	Band Anticrossing in III-V Alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2001 , 223, 75-85	1.3	107
473	A comparative study of phase stability and film morphology in thin-film M/GaAs systems (M=Co, Rh, Ir, Ni, Pd, and Pt). <i>Journal of Applied Physics</i> , 1987 , 62, 2070-2079	2.5	104
472	Dependence of the fundamental band gap of Al _x Ga _{1-x} N on alloy composition and pressure. <i>Journal of Applied Physics</i> , 1999 , 85, 8505-8507	2.5	100
471	On the crystalline structure, stoichiometry and band gap of InN thin films. <i>Applied Physics Letters</i> , 2005 , 86, 071910	3.4	97
470	. <i>IEEE Transactions on Plasma Science</i> , 1993 , 21, 440-446	1.3	93
469	Universal bandgap bowing in group-III nitride alloys. <i>Solid State Communications</i> , 2003 , 127, 411-414	1.6	92
468	Reduction of band-gap energy in GaNAs and AlGaNAs synthesized by N ⁺ implantation. <i>Applied Physics Letters</i> , 1999 , 75, 1410-1412	3.4	90
467	Effect of nitrogen on the electronic band structure of group III-N-V alloys. <i>Physical Review B</i> , 2000 , 62, 4211-4214	3.3	89
466	Ferromagnetism in Ga(1-x)Mn(x)P: evidence for inter-Mn exchange mediated by localized holes within a detached impurity band. <i>Physical Review Letters</i> , 2005 , 95, 207204	7.4	87

465	Two-photon excitation in an intermediate band solar cell structure. <i>Applied Physics Letters</i> , 2012 , 100, 172111	3.4	83
464	Curie temperature limit in ferromagnetic Ga _{1-x} MnxAs. <i>Physical Review B</i> , 2003 , 68,	3.3	83
463	Highly uniform and stable n-type carbon nanotube transistors by using positively charged silicon nitride thin films. <i>Nano Letters</i> , 2015 , 15, 392-7	11.5	82
462	Pressure-dependent photoluminescence study of ZnO nanowires. <i>Applied Physics Letters</i> , 2005 , 86, 1531-1534	3.7	80
461	Ferromagnetic Ga _{1-x} MnxAs produced by ion implantation and pulsed-laser melting. <i>Applied Physics Letters</i> , 2003 , 82, 1251-1253	3.4	80
460	Effect of band anticrossing on the optical transitions in GaAs _{1-x} Nx/GaAs multiple quantum wells. <i>Physical Review B</i> , 2001 , 64,	3.3	80
459	Simultaneous Enhancement of Electrical Conductivity and Thermopower of Bi ₂ Te ₃ by Multifunctionality of Native Defects. <i>Advanced Materials</i> , 2015 , 27, 3681-6	24	79
458	Characterization of GaAs layers grown by low temperature molecular beam epitaxy using ion beam techniques. <i>Journal of Applied Physics</i> , 1992 , 72, 2850-2856	2.5	79
457	Growth and properties of GaSbBi alloys. <i>Applied Physics Letters</i> , 2013 , 103, 142106	3.4	78
456	Large kinetic asymmetry in the metal-insulator transition nucleated at localized and extended defects. <i>Physical Review B</i> , 2011 , 83,	3.3	78
455	Plasma synthesis of metallic and composite thin films with atomically mixed substrate bonding. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1993 , 80-81, 1281-1287	1.2	77
454	Valence band hybridization in N-rich GaN _{1-x} Asx alloys. <i>Physical Review B</i> , 2004 , 70,	3.3	76
453	Existence and removal of Cu ₂ Se second phase in coevaporated Cu ₂ ZnSnSe ₄ thin films. <i>Journal of Applied Physics</i> , 2012 , 111, 053522	2.5	74
452	On-Nanowire Axial Heterojunction Design for High-Performance Photodetectors. <i>ACS Nano</i> , 2016 , 10, 8474-81	16.7	73
451	Effect of oxygen on the electronic band structure in ZnOxSe _{1-x} alloys. <i>Applied Physics Letters</i> , 2003 , 83, 299-301	3.4	70
450	Ideal transparent conductors for full spectrum photovoltaics. <i>Journal of Applied Physics</i> , 2012 , 111, 123505	3.5	69
449	Enhancement of Curie temperature in Ga _{1-x} MnxAs/Ga _{1-y} AlyAs ferromagnetic heterostructures by Be modulation doping. <i>Applied Physics Letters</i> , 2003 , 83, 4220-4222	3.4	67
448	In _{1-x} MnxSb _x narrow-gap ferromagnetic semiconductor. <i>Applied Physics Letters</i> , 2003 , 82, 4310-4312	3.4	67

447	Hole transport and photoluminescence in Mg-doped InN. <i>Journal of Applied Physics</i> , 2010 , 107, 113712	2.5	62
446	Band gap bowing parameter of In _{1-x} Al _x N. <i>Journal of Applied Physics</i> , 2008 , 104, 123501	2.5	62
445	Band anticrossing in GaP _{1-x} N _x alloys. <i>Physical Review B</i> , 2002 , 65,	3.3	62
444	Origin of the large band-gap bowing in highly mismatched semiconductor alloys. <i>Physical Review B</i> , 2003 , 67,	3.3	61
443	High Bi content GaSbBi alloys. <i>Journal of Applied Physics</i> , 2014 , 116, 043511	2.5	60
442	Nitrogen-induced increase of the maximum electron concentration in group III-N-V alloys. <i>Physical Review B</i> , 2000 , 61, R13337-R13340	3.3	60
441	Band anticrossing in highly mismatched Sn _x Ge _{1-x} semiconducting alloys. <i>Physical Review B</i> , 2008 , 77,	3.3	59
440	Pressure dependence of the fundamental band-gap energy of CdSe. <i>Applied Physics Letters</i> , 2004 , 84, 67-69	3.4	58
439	Effects of surface states on electrical characteristics of InN and In _{1-x} Ga _x N. <i>Physical Review B</i> , 2007 , 76,	3.3	57
438	Synthesis and optical properties of II-O-VI highly mismatched alloys. <i>Journal of Applied Physics</i> , 2004 , 95, 6232-6238	2.5	55
437	Fermi level stabilization energy in cadmium oxide. <i>Journal of Applied Physics</i> , 2010 , 107, 113706	2.5	54
436	Highly mismatched crystalline and amorphous GaN _{1-x} As _x alloys in the whole composition range. <i>Journal of Applied Physics</i> , 2009 , 106, 103709	2.5	54
435	Demonstration of a III-Nitride/Silicon Tandem Solar Cell. <i>Applied Physics Express</i> , 2009 , 2, 122202	2.4	54
434	Effect of charged dislocation scattering on electrical and electrothermal transport in n-type InN. <i>Physical Review B</i> , 2011 , 84,	3.3	53
433	Mg-doped InN and InGaN [Photoluminescence, capacitance-voltage and thermopower measurements. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 873-877	1.3	53
432	Crystal structure and properties of Cd _x Zn _{1-x} O alloys across the full composition range. <i>Applied Physics Letters</i> , 2013 , 102, 232103	3.4	52
431	Structural and optical quality of GaN/metal/Si heterostructures fabricated by excimer laser lift-off. <i>Applied Physics Letters</i> , 1999 , 75, 1887-1889	3.4	52
430	Mechanism of stress relaxation in Ge nanocrystals embedded in SiO ₂ . <i>Applied Physics Letters</i> , 2005 , 86, 063107	3.4	51

429	Mutual passivation of electrically active and isovalent impurities. <i>Nature Materials</i> , 2002 , 1, 185-9	27	51
428	Molecular beam epitaxial growth and optical properties of highly mismatched ZnTe _{1-x} O _x alloys. <i>Applied Physics Letters</i> , 2012 , 100, 011905	3-4	50
427	Photocurrent induced by two-photon excitation in ZnTeO intermediate band solar cells. <i>Applied Physics Letters</i> , 2013 , 102, 052111	3-4	50
426	Band structure engineering of ZnO _{1-x} Sex alloys. <i>Applied Physics Letters</i> , 2010 , 97, 022104	3-4	50
425	Ion-dose-dependent microstructure in amorphous Ge. <i>Physical Review B</i> , 2000 , 61, 12586-12589	3-3	48
424	Universal and Solution-Processable Precursor to Bismuth Chalcogenide Thermoelectrics. <i>Chemistry of Materials</i> , 2010 , 22, 1943-1945	9.6	47
423	Theoretical and experimental studies of electronic band structure for GaSb _{1-x} Bix in the dilute Bi regime. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 355107	3	46
422	High quality ZnO:Al transparent conducting oxide films synthesized by pulsed filtered cathodic arc deposition. <i>Thin Solid Films</i> , 2010 , 518, 3313-3319	2.2	46
421	Electron mobility in InN and III-N alloys. <i>Journal of Applied Physics</i> , 2007 , 102, 073705	2.5	46
420	Structure-Dependent Hydrostatic Deformation Potentials of Individual Single-Walled Carbon Nanotubes. <i>Physical Review Letters</i> , 2004 , 93,	7.4	46
419	Determination of free hole concentration in ferromagnetic Ga _{1-x} MnxAs using electrochemical capacitance-voltage profiling. <i>Applied Physics Letters</i> , 2002 , 81, 844-846	3-4	44
418	Electronic structure of Ga _{1-x} MnxAs analyzed according to hole-concentration-dependent measurements. <i>Physical Review B</i> , 2010 , 81,	3-3	43
417	Synthesis of GaN _x As _{1-x} thin films by pulsed laser melting and rapid thermal annealing of N ⁺ -implanted GaAs. <i>Journal of Applied Physics</i> , 2003 , 94, 1043-1049	2.5	43
416	Structural and electronic properties of amorphous and polycrystalline In ₂ Se ₃ films. <i>Journal of Applied Physics</i> , 2003 , 94, 2390-2397	2.5	42
415	Characterization of the local structure of amorphous GaAs produced by ion implantation. <i>Journal of Applied Physics</i> , 1998 , 83, 4610-4614	2.5	42
414	Growth of III-V thin films from single-source precursors based on sterically encumbered sited ligands. <i>Journal of Crystal Growth</i> , 1992 , 124, 647-653	1.6	42
413	Mg doped InN and confirmation of free holes in InN. <i>Applied Physics Letters</i> , 2011 , 98, 042104	3-4	41
412	Electrical activation and electron spin resonance measurements of implanted bismuth in isotopically enriched silicon-28. <i>Applied Physics Letters</i> , 2012 , 100, 172104	3-4	41

411	Formation of Mn-derived impurity band in III-Mn-V alloys by valence band anticrossing. <i>Physical Review B</i> , 2008 , 78,	3-3	41
410	Compensating point defects in He+4-irradiated InN. <i>Physical Review B</i> , 2007 , 75,	3-3	41
409	Effects of Free Carriers on the Optical Properties of Doped CdO for Full-Spectrum Photovoltaics. <i>Physical Review Applied</i> , 2016 , 6,	4-3	41
408	Temperature dependence of the band gap of GaSb _{1-x} Bi _x alloys with 0 < x < 1. <i>Applied Physics Letters</i> , 2013 , 103, 261907	3-4	40
407	High temperature behavior of Pt and Pd on GaN. <i>Journal of Applied Physics</i> , 1997 , 81, 3134-3137	2-5	40
406	Schottky barrier degradation of the W/GaAs system after high-temperature annealing. <i>Journal of Applied Physics</i> , 1986 , 60, 3235-3242	2-5	40
405	Fermi-level stabilization in the topological insulators Bi ₂ Se ₃ and Bi ₂ Te ₃ : Origin of the surface electron gas. <i>Physical Review B</i> , 2014 , 89,	3-3	39
404	Synthesis of In _x P _{1-x} thin films by N ion implantation. <i>Applied Physics Letters</i> , 2001 , 78, 1077-1079	3-4	39
403	Bi-induced band gap reduction in epitaxial InSbBi alloys. <i>Applied Physics Letters</i> , 2014 , 105, 212101	3-4	38
402	Metalorganic Chemical Vapor Deposition of Semiconducting III/VI In ₂ Se ₃ Thin Films from the Single-Source Precursor: In[SeC(SiMe ₃) ₃] ₃ . <i>Chemistry of Materials</i> , 1995 , 7, 2273-2276	9-6	38
401	Formation of diluted III _N nitride thin films by N ion implantation. <i>Journal of Applied Physics</i> , 2001 , 90, 2227-2234	2-5	37
400	Growth and characterization of ZnO _{1-x} S _x highly mismatched alloys over the entire composition. <i>Journal of Applied Physics</i> , 2015 , 118, 215702	2-5	36
399	Full multiple scattering analysis of XANES at the Cd L ₃ and O K edges in CdO films combined with a soft-x-ray emission investigation. <i>Physical Review B</i> , 2010 , 82,	3-3	36
398	Effects of point defects on thermal and thermoelectric properties of InN. <i>Applied Physics Letters</i> , 2011 , 98, 012108	3-4	36
397	Composition-dependent bond lengths in crystalline and amorphized Ge _x Si _{1-x} alloys. <i>Physical Review B</i> , 1999 , 60, 10831-10836	3-3	36
396	Stable, freestanding Ge nanocrystals. <i>Journal of Applied Physics</i> , 2005 , 97, 124316	2-5	35
395	Band-gap bowing effects in B _x Ga _{1-x} As alloys. <i>Journal of Applied Physics</i> , 2003 , 93, 2696-2699	2-5	35
394	Room-Temperature Red-Green-Blue Whispering-Gallery Mode Lasing and White-Light Emission from Cesium Lead Halide Perovskite (CsPbX ₃ , X = Cl, Br, I) Microstructures. <i>Advanced Optical Materials</i> , 2018 , 6, 1700993	8-1	33

393	Demonstration of homojunction ZnTe solar cells. <i>Journal of Applied Physics</i> , 2010 , 108, 024502	2.5	33
392	Growth and properties of ferromagnetic In _{1-x} MnxSb alloys. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 20, 325-332	3	33
391	Lattice location of diffused Zn atoms in GaAs and InP single crystals. <i>Journal of Applied Physics</i> , 1991 , 69, 2998-3006	2.5	33
390	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 112105	3.4	32
389	Metal-insulator transition by isovalent anion substitution in Ga _{1-x} MnxAs: implications to ferromagnetism. <i>Physical Review Letters</i> , 2008 , 101, 087203	7.4	32
388	High-temperature Hall effect in Ga _{1-x} MnxAs. <i>Physical Review B</i> , 2004 , 69,	3.3	32
387	High-temperature annealing characteristics of tungsten and tungsten nitride Schottky contacts to GaAs under different annealing conditions. <i>Journal of Applied Physics</i> , 1988 , 64, 1284-1291	2.5	32
386	Fermi level stabilization and band edge energies in Cd _x Zn _{1-x} O alloys. <i>Journal of Applied Physics</i> , 2014 , 115, 233708	2.5	31
385	GaN _{1-x} Bix: Extremely mismatched semiconductor alloys. <i>Applied Physics Letters</i> , 2010 , 97, 141919	3.4	31
384	Characterization of low-temperature molecular-beam-epitaxy grown GaBiAs layers. <i>Semiconductor Science and Technology</i> , 2007 , 22, 819-823	1.8	31
383	Synthesis of GaN nanocrystals by sequential ion implantation. <i>Applied Physics Letters</i> , 1997 , 70, 2268-2270	3.4	30
382	Band anticrossing in group II-Ox _{1-x} highly mismatched alloys: Cd _{1-x} MnyOxTe _{1-x} quaternaries synthesized by O ion implantation. <i>Applied Physics Letters</i> , 2002 , 80, 1571-1573	3.4	30
381	Optimization of Ge/C ratio for compensation of misfit strain in solid phase epitaxial growth of SiGe layers. <i>Applied Physics Letters</i> , 1993 , 63, 2682-2684	3.4	30
380	Coimplantation and electrical activity of C in GaAs: Stoichiometry and damage effects. <i>Applied Physics Letters</i> , 1992 , 60, 2383-2385	3.4	30
379	Electrical transport and ferromagnetism in Ga _{1-x} MnxAs synthesized by ion implantation and pulsed-laser melting. <i>Journal of Applied Physics</i> , 2008 , 103, 073913	2.5	29
378	High electron mobility InN. <i>Applied Physics Letters</i> , 2007 , 90, 162103	3.4	29
377	Doping and defect control of ferromagnetic semiconductors formed by ion implantation and pulsed-laser melting. <i>Physica B: Condensed Matter</i> , 2006 , 376-377, 630-634	2.8	29
376	Effect of film thickness on the incorporation of Mn interstitials in Ga _{1-x} MnxAs. <i>Applied Physics Letters</i> , 2005 , 86, 042102	3.4	27

375	MnL3,2 x-ray absorption and magnetic circular dichroism in ferromagnetic Ga1-xMnxP. <i>Applied Physics Letters</i> , 2006 , 89, 012504	3.4	27
374	Enhanced nitrogen incorporation by pulsed laser annealing of GaNxAs1-x formed by N ion implantation. <i>Applied Physics Letters</i> , 2002 , 80, 3958-3960	3.4	27
373	Nitrogen-induced enhancement of the free electron concentration in sulfur implanted GaNxAs1-x. <i>Applied Physics Letters</i> , 2000 , 77, 2858-2860	3.4	27
372	Reduction of threading dislocation density in GaN using an intermediate temperature interlayer. <i>Applied Physics Letters</i> , 2000 , 77, 3562-3564	3.4	27
371	Band anticrossing in dilute nitrides. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, S3355-S3372	1.8	26
370	Defects and properties of cadmium oxide based transparent conductors. <i>Journal of Applied Physics</i> , 2016 , 119, 181501	2.5	26
369	Electronic effects determining the formation of ferromagnetic III1-xMnxV alloys during epitaxial growth. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 25, 171-180	3	25
368	Diluted magnetic semiconductors formed by ion implantation and pulsed-laser melting. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 908-912	2.8	25
367	Structural-relaxation-induced bond length and bond angle changes in amorphized Ge. <i>Physical Review B</i> , 2001 , 63,	3.3	25
366	Effects of rapid quenching on the impurity site location in Zn-diffused InP. <i>Journal of Applied Physics</i> , 1993 , 74, 86-90	2.5	25
365	Electronic band structure of ZnO-rich highly mismatched ZnO1-xTex alloys. <i>Applied Physics Letters</i> , 2015 , 106, 092101	3.4	24
364	Bi flux-dependent MBE growth of GaSbBi alloys. <i>Journal of Crystal Growth</i> , 2015 , 425, 241-244	1.6	24
363	Highly mismatched N-rich GaN1-xSbx films grown by low temperature molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 102104	3.4	24
362	Embedded binary eutectic alloy nanostructures: a new class of phase change materials. <i>Nano Letters</i> , 2010 , 10, 2794-8	11.5	24
361	Electrical properties of InGaN-Si heterojunctions. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S413-S416		24
360	Native-defect-controlled n-type conductivity in InN. <i>Physica B: Condensed Matter</i> , 2006 , 376-377, 436-439	2.8	24
359	Cross-section transmission electron microscopy study of carbon-implanted layers in silicon. <i>Applied Physics Letters</i> , 1990 , 57, 798-800	3.4	24
358	Electronic band structure of highly mismatched GaN1-xSbx alloys in a broad composition range. <i>Applied Physics Letters</i> , 2015 , 107, 142104	3.4	23

357	Lattice site locations of excess arsenic atoms in gallium arsenide grown by low-temperature molecular beam epitaxy. <i>Applied Physics Letters</i> , 1991 , 59, 3267-3269	3.4	23
356	Effects of interface reactions on electrical characteristics of metal-GaAs contacts. <i>Applied Physics Letters</i> , 1987 , 51, 189-191	3.4	23
355	Self-generated oscillations in continuous crystallizers: Part I. Analytical prediction of the oscillating output. <i>AIChE Journal</i> , 1975 , 21, 917-924	3.6	23
354	Charge transfer and mobility enhancement at CdO/SnTe heterointerfaces. <i>Applied Physics Letters</i> , 2014 , 105, 132103	3.4	22
353	Electronic structure of CdO studied by soft X-ray spectroscopy. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2011 , 184, 249-253	1.7	22
352	Diluted ZnMnTe oxide: a multi-band semiconductor for high efficiency solar cells. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 660-663	1.3	22
351	Structural characterization of low-temperature molecular beam epitaxial In _{0.52} Al _{0.48} As/InP heterolayers. <i>Applied Physics Letters</i> , 1992 , 60, 989-991	3.4	22
350	Solid-phase reactions between (100) GaAs and thin-film refractory metals (Ti, Zr, V, Nb, Cr, Mo, and W). <i>Applied Physics A: Solids and Surfaces</i> , 1987 , 44, 177-190		22
349	Vacancy defects induced changes in the electronic and optical properties of NiO studied by spectroscopic ellipsometry and first-principles calculations. <i>Journal of Applied Physics</i> , 2020 , 128, 135705 ²⁻⁵		22
348	Self-Passivation of Defects: Effects of High-Energy Particle Irradiation on the Elastic Modulus of Multilayer Graphene. <i>Advanced Materials</i> , 2015 , 27, 6841-7	24	21
347	p-type InN and In-rich InGaN. <i>Physica Status Solidi (B): Basic Research</i> , 2007 , 244, 1820-1824	1.3	21
346	Structural properties of Ge nanocrystals embedded in sapphire. <i>Journal of Applied Physics</i> , 2006 , 100, 114317	2.5	21
345	Multiphonon resonance Raman scattering in In _x Ga _{1-x} N. <i>Physical Review B</i> , 2005 , 72,	3.3	21
344	Increasing the retained dose by plasma immersion ion implantation and deposition. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1995 , 102, 132-135	1.2	21
343	Strain-engineered ferromagnetic In _{1-x} Mn _x As films with in-plane easy axis. <i>Applied Physics Letters</i> , 2005 , 86, 112512	3.4	20
342	Narrow bandgap group III-nitride alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2003 , 240, 412-416	1.3	20
341	. <i>IEEE Journal of Photovoltaics</i> , 2013 , 3, 730-736	3.7	19
340	Material properties of Cd _{1-x} Mg _x O alloys synthesized by radio frequency sputtering. <i>Applied Physics Letters</i> , 2013 , 103, 041902	3.4	19

339	Molecular beam epitaxy of crystalline and amorphous GaN layers with high As content. <i>Journal of Crystal Growth</i> , 2009 , 311, 3417-3422	1.6	19
338	Properties of Ga _{1-x} MnxAs with high x (>0.1). <i>Journal of Applied Physics</i> , 2008 , 103, 07D136	2.5	19
337	Structural characterization of amorphized InP: Evidence for chemical disorder. <i>Applied Physics Letters</i> , 1999 , 74, 1713-1715	3.4	19
336	Growth and characterization of highly mismatched GaN _{1-x} Sbx alloys. <i>Journal of Applied Physics</i> , 2014 , 116, 123704	2.5	18
335	. <i>IEEE Journal of Photovoltaics</i> , 2014 , 4, 196-201	3.7	18
334	Common structure in amorphised compound semiconductors. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2003 , 199, 235-239	1.2	18
333	Effect of native defects on optical properties of In _x Ga _{1-x} N alloys. <i>Applied Physics Letters</i> , 2005 , 87, 1619054	3.4	18
332	Growth behavior of co-electrodeposited CZTS precursor thin films from acidic baths containing tartaric acid. <i>Materials Chemistry and Physics</i> , 2018 , 204, 83-94	4.4	17
331	Band Gap Engineering of Oxide Photoelectrodes: Characterization of ZnO _{1-x} Sex. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 15281-15289	3.8	17
330	Modification of (Pb,La)(Zr,Ti)O ₃ thin films during pulsed laser liftoff from MgO substrates. <i>Journal of Applied Physics</i> , 2003 , 94, 4047-4052	2.5	17
329	Compositional modulation in In(x)Ga(1-x)N: TEM and X-ray studies. <i>Microscopy (Oxford, England)</i> , 2005 , 54, 243-50	1.3	17
328	Local structures of free-standing Al _x Ga _{1-x} N thin films studied by extended x-ray absorption fine structure. <i>Applied Physics Letters</i> , 1999 , 75, 4097-4099	3.4	17
327	Cathodic arc deposition of copper oxide thin films. <i>Surface and Coatings Technology</i> , 1996 , 78, 168-172	4.4	17
326	Plasma immersion Pd ion implantation seeding pattern formation for selective electroless Cu plating. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1991 , 55, 888-892	1.2	17
325	NixCd _{1-x} O: Semiconducting alloys with extreme type III band offsets. <i>Applied Physics Letters</i> , 2015 , 106, 022110	3.4	16
324	Low gap amorphous GaN _{1-x} Asx alloys grown on glass substrate. <i>Applied Physics Letters</i> , 2010 , 97, 1019063	3.4	16
323	Phase separation in annealed InGaN/GaN multiple quantum wells. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 33-36	1.6	16
322	Effects of donor doping on Ga _{1-x} MnxAs. <i>Applied Physics Letters</i> , 2008 , 93, 262505	3.4	16

321	Low-temperature grown compositionally graded InGaN films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1866-1869		16
320	Direct evidence of the Fermi-energy-dependent formation of Mn interstitials in modulation-doped Ga _{1-x} Al _y As/Ga _{1-x} Mn _x As/Ga _{1-x} Al _y As heterostructures. <i>Applied Physics Letters</i> , 2004 , 84, 4325-4327	3-4	16
319	Composition dependence of the hydrostatic pressure coefficients of the bandgap of ZnSe _{1-x} Te _x alloys. <i>Physical Review B</i> , 2003 , 68,	3-3	16
318	Mutual passivation of group IV donors and nitrogen in diluted Ga _x N _{1-x} As alloys. <i>Applied Physics Letters</i> , 2003 , 83, 2844-2846	3-4	16
317	Direct evidence of defect annihilation during structural relaxation of amorphous indium phosphide. <i>Physical Review B</i> , 2003 , 68,	3-3	16
316	Correlation between solid-state reaction and electrical properties of the Rh/GaAs Schottky contact. <i>Journal of Applied Physics</i> , 1987 , 61, 1099-1102	2-5	16
315	Organic Hybrid Perovskite (MAPbI _{3-x} Cl _x) for Thermochromic Smart Window with Strong Optical Regulation Ability, Low Transition Temperature, and Narrow Hysteresis Width. <i>Advanced Functional Materials</i> , 2021 , 31, 2010426	15.6	16
314	Temperature evolution of carrier dynamics in Ga _x N _{1-x} PyAs _{1-y} alloys. <i>Journal of Applied Physics</i> , 2015 , 117, 175702	2-5	15
313	Demonstration of ZnTe _{1-x} O _x Intermediate Band Solar Cell. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 082304	1-4	15
312	Molecular beam epitaxy of InGaN thin films on Si(111): Effect of substrate nitridation. <i>Thin Solid Films</i> , 2009 , 517, 6512-6515	2-2	15
311	Growth and transport properties of p-type GaN _{1-x} Bi _x alloys. <i>Journal of Materials Research</i> , 2011 , 26, 2887-2894		15
310	Tuning of ferromagnetism through anion substitution in Ga _{1-x} Mn _x pnictide ferromagnetic semiconductors. <i>Physica B: Condensed Matter</i> , 2007 , 401-402, 454-457	2-8	15
309	Single crystal growth and properties of ε phase in the CuInSe ₂ +2CdS \rightleftharpoons CuInS ₂ +2CdSe reciprocal system. <i>Solar Energy Materials and Solar Cells</i> , 2008 , 92, 1495-1499	6-4	15
308	Compositional modulation in. <i>Physica B: Condensed Matter</i> , 2006 , 376-377, 468-472	2-8	15
307	Electrical activity and precipitation behavior of copper in gallium arsenide. <i>Applied Physics A: Materials Science and Processing</i> , 1995 , 61, 7-16	2-6	15
306	Formation of semi-insulating InP through metallic Cu-rich precipitates. <i>Physical Review B</i> , 1992 , 46, 12460-12468	9-3	15
305	Crystalline all-inorganic lead-free Cs ₃ Sb ₂ I ₉ perovskite microplates with ultra-fast photoconductive response and robust thermal stability. <i>Nano Research</i> , 1	10	15
304	Band structure of germanium carbides for direct bandgap silicon photonics. <i>Journal of Applied Physics</i> , 2016 , 120, 053102	2-5	15

303	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. <i>Semiconductor Science and Technology</i> , 2015 , 30, 085018	1.8	14
302	Surface photovoltage and modulation spectroscopy of E ₁ and E ₁ ⁺ transitions in GaNAs layers. <i>Thin Solid Films</i> , 2014 , 567, 101-104	2.2	14
301	Heat flow model for pulsed laser melting and rapid solidification of ion implanted GaAs. <i>Journal of Applied Physics</i> , 2010 , 108, 013508	2.5	14
300	Non-equilibrium GaNAs alloys with band gap ranging from 0.8-3.4 eV. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 1847-1849		14
299	Mutual passivation effects in Si-doped diluted In _y Ga _{1-y} As _{1-x} N _x alloys. <i>Physical Review B</i> , 2003 , 68,	3.3	14
298	Ion beam synthesis and n-type doping of group III _x IV _{1-x} alloys. <i>Semiconductor Science and Technology</i> , 2002 , 17, 785-796	1.8	14
297	Substitutionality of Ge atoms in ion implanted AlSb. <i>Applied Physics Letters</i> , 1995 , 66, 2406-2408	3.4	14
296	Pulsed Excimer Laser Processing of AlN/GaN Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 449, 1011		14
295	Phase Formation Sequence in the Pd-GaAs System. <i>Materials Research Society Symposia Proceedings</i> , 1985 , 54, 367		14
294	Self-Densified Optically Transparent VO Thermochromic Wood Film for Smart Windows. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 22495-22504	9.5	14
293	Stoichiometry Controlled Bipolar Conductivity in Nanocrystalline Ni _x Cd _{1-x} O _{1+δ} Thin Films. <i>Physical Review Applied</i> , 2019 , 11,	4.3	13
292	Highly mismatched GaN _{1-x} Sb _x alloys: synthesis, structure and electronic properties. <i>Semiconductor Science and Technology</i> , 2016 , 31, 083001	1.8	13
291	GaN _{1-x} Sb _x highly mismatched alloys grown by low temperature molecular beam epitaxy under Ga-rich conditions. <i>Journal of Crystal Growth</i> , 2013 , 383, 95-99	1.6	13
290	Molecular beam epitaxy of GaNAs alloys with high As content for potential photoanode applications in hydrogen production. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010 , 28, C3B12-C3B16	1.3	13
289	Structural perfection of InGaN layers and its relation to photoluminescence. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 2626-2631		13
288	Red-green luminescence in indium gallium nitride alloys investigated by high pressure optical spectroscopy. <i>Applied Physics Letters</i> , 2012 , 100, 162103	3.4	13
287	Structural and optical studies of nitrogen incorporation into GaSb-based GaInSb quantum wells. <i>Applied Physics Letters</i> , 2012 , 100, 021103	3.4	13
286	High quality In _x Ga _{1-x} N thin films with x > 0.2 grown on silicon. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1747-1749	1.3	13

285	Epitaxial growth of CdSexTe1-x thin films on Si(100) by molecular beam epitaxy using lattice mismatch graded structures. <i>Journal of Crystal Growth</i> , 2008 , 310, 1081-1087	1.6	13
284	Structural characterization of amorphised InAs with synchrotron radiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2002 , 190, 851-855	1.2	13
283	Band anticrossing effects in MgyZn1-yTe1-xSex alloys. <i>Applied Physics Letters</i> , 2002 , 80, 34-36	3.4	13
282	Formation of iridium silicide layer by high dose iridium ion implantation into silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1991 , 58, 27-33	1.2	13
281	Characterization of strained InGaAs single quantum well structures by ion beam methods. <i>Applied Physics Letters</i> , 1990 , 56, 45-47	3.4	13
280	Growth studies of pseudomorphic GaAs/InGaAs/AlGaAs modulation-doped field-effect transistor structures. <i>Applied Physics Letters</i> , 1990 , 56, 2022-2024	3.4	13
279	Interfacial interactions of evaporated iridium thin films with (100) GaAs. <i>Journal of Applied Physics</i> , 1987 , 62, 1815-1820	2.5	13
278	Investigations of thin films on GaAs using the proton resonant scattering technique. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1988 , 30, 551-556	1.2	13
277	Rapid thermal annealing assisted facile solution method for tungsten-doped vanadium dioxide thin films on glass substrate. <i>Journal of Alloys and Compounds</i> , 2020 , 833, 155053	5.7	12
276	Modeling of the atomic structure and electronic properties of amorphous GaN1-xAsx. <i>Computational Materials Science</i> , 2014 , 82, 100-106	3.2	12
275	Molecular beam epitaxy of highly mismatched N-rich GaN1-xSbx and InN1-xAsx alloys. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C102	1.3	12
274	Compositional dependence of ferromagnetism in (Al,Ga,Mn)As magnetic semiconductors. <i>Physical Review B</i> , 2008 , 78,	3.3	12
273	Photoluminescence of energetic particle-irradiated InxGa1-xN alloys. <i>Applied Physics Letters</i> , 2006 , 88, 151101	3.4	12
272	Dopants and defects in InN and InGaN alloys. <i>Journal of Crystal Growth</i> , 2006 , 288, 278-282	1.6	12
271	Correlation of Mn Lattice Location, Free Hole Concentration, and Curie Temperature in Ferromagnetic GaMnAs. <i>Journal of Superconductivity and Novel Magnetism</i> , 2003 , 16, 41-44		12
270	Mechanisms of dislocation reduction in GaN using an intermediate temperature interlayer. <i>Journal of Electronic Materials</i> , 2001 , 30, 1417-1420	1.9	12
269	Influence of microstructure on electrical properties of diluted GaNxAs1-x formed by nitrogen implantation. <i>Applied Physics Letters</i> , 2001 , 79, 931-933	3.4	12
268	Increased electrical activation in the near-surface region of sulfur and nitrogen coimplanted GaAs. <i>Applied Physics Letters</i> , 2000 , 77, 3607-3609	3.4	12

267	Defect control during solid phase epitaxial growth of SiGe alloy layers. <i>Applied Physics Letters</i> , 1993 , 63, 929-931	3.4	12
266	Metal vapor vacuum arc ion implantation for seeding of electroless Cu plating. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1991 , 55, 893-897	1.2	12
265	Applications of Heavy-Ion Rutherford Backscattering Spectrometry (HIRBS) to the analysis of contact structures on GaAs and Ge. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1985 , 10-11, 606-610	1.2	12
264	Controllable optical emission wavelength in all-inorganic halide perovskite alloy microplates grown by two-step chemical vapor deposition. <i>Nano Research</i> , 2020 , 13, 2939-2949	10	12
263	Multicolor emission from intermediate band semiconductor ZnOSe. <i>Scientific Reports</i> , 2017 , 7, 44214	4.9	11
262	Room-Temperature-Synthesized High-Mobility Transparent Amorphous CdO-GaO Alloys with Widely Tunable Electronic Bands. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 7239-7247	9.5	11
261	InGaN doping for high carrier concentration in plasma-assisted molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 381-384		11
260	Molecular beam epitaxial growth of ZnCdTeO epilayers for intermediate band solar cells. <i>Journal of Crystal Growth</i> , 2013 , 378, 259-262	1.6	11
259	In-rich InGaN thin films: Progress on growth, compositional uniformity, and doping for device applications. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C114	1.3	11
258	P-type InGaN across the entire alloy composition range. <i>Applied Physics Letters</i> , 2013 , 102, 102111	3.4	11
257	Spontaneous stratification of InGaN layers and its influence on optical properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S433-S436		11
256	Edetected NMR of Li in Ga _{1-x} Mn _x As. <i>Physical Review B</i> , 2011 , 84,	3.3	11
255	Decoupling single nanowire mobilities limited by surface scattering and bulk impurity scattering. <i>Journal of Applied Physics</i> , 2011 , 110, 033705	2.5	11
254	Nonmagnetic compensation in ferromagnetic Ga _{1-x} Mn _x As and Ga _{1-x} Mn _x P synthesized by ion implantation and pulsed-laser melting. <i>Journal of Applied Physics</i> , 2008 , 103, 123906	2.5	11
253	Micro- and macro-structure of implantation-induced disorder in Ge. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000 , 161-163, 1033-1037	1.2	11
252	The Influence of X-Ray Irradiation on Structural Relaxation and Crystallization of Amorphous Silicon Films. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 5890-5893	1.4	11
251	Growth and characterization of ZnSe grown by organometallic vapor phase epitaxy using diisopropyl selenide and diethyl zinc. <i>Journal of Crystal Growth</i> , 1995 , 147, 47-54	1.6	11
250	Anomalous ion damage behavior in ZnSe. <i>Applied Physics Letters</i> , 1996 , 69, 2062-2064	3.4	11

- 249 Anomalies in annealed LT-GaAs samples. *Journal of Electronic Materials*, **1993**, 22, 1395-1399 1.9 11
- 248 Investigation of Metal/GaAs Reactions by Heavy Ion Rutherford Backscattering Spectrometry(HIRBS). *Materials Research Society Symposia Proceedings*, **1986**, 69, 281 11
- 247 Wide-Gap Zn_{1-x}Ni_xO Alloy: A Transparent p-Type Oxide. *Physical Review Applied*, **2020**, 13, 4-3 10
- 246 Multicolor Electroluminescence from Intermediate Band Solar Cell Structures. *Advanced Energy Materials*, **2016**, 6, 1501820 21.8 10
- 245 Molecular beam epitaxy of GaN_{1-x}Bi_x alloys with high bismuth content. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 419-423 1.6 10
- 244 Growth by molecular beam epitaxy of amorphous and crystalline GaNAs alloys with band gaps from 3.4 to 0.8 eV for solar energy conversion devices. *Journal of Crystal Growth*, **2011**, 323, 60-63 1.6 10
- 243 Electrical and electrothermal transport in InN: The roles of defects. *Physica B: Condensed Matter*, **2009**, 404, 4862-4865 2.8 10
- 242 Defect redistribution in postirradiation rapid-thermal-annealed InN. *Physical Review B*, **2010**, 82, 3-3 10
- 241 Self-neutralized ion implantation into insulators. *Nuclear Instruments & Methods in Physics Research B*, **1997**, 132, 188-192 1.2 10
- 240 Compositional tuning of ferromagnetism in Ga_{1-x}Mn_xP. *Solid State Communications*, **2006**, 140, 443-446 1.6 10
- 239 Effects of pressure on the band structure of highly mismatched Zn_{1-x}MnyOxTe_{1-x} alloys. *Applied Physics Letters*, **2004**, 84, 924-926 3-4 10
- 238 Solid-state reaction in Pd/ZnSe thin film contacts. *Applied Physics Letters*, **1995**, 67, 947-949 3-4 10
- 237 Formation of Buried Epitaxial Si-Ge Alloy Layers in Si Crystal by High Dose Ge ION Implantation. *Materials Research Society Symposia Proceedings*, **1991**, 235, 293 10
- 236 . *IEEE Journal of Photovoltaics*, **2017**, 7, 1024-1030 3-7 9
- 235 Effects of the d-donor level of vanadium on the properties of Zn_{1-x}V_xO films. *Applied Physics Letters*, **2015**, 106, 182101 3-4 9
- 234 Room temperature sputtered Cu doped NiO_{1+x}p-type conductivity, stability of electrical properties and p-n heterojunction. *Journal of Alloys and Compounds*, **2020**, 835, 155269 5-7 9
- 233 Substitutionality of nitrogen atoms and formation of nitrogen complexes and point defects in GaPN alloys. *Journal Physics D: Applied Physics*, **2014**, 47, 075106 3 9
- 232 Effects of Ni d-levels on the electronic band structure of Ni_xCd_{1-x}O semiconducting alloys. *Journal of Applied Physics*, **2017**, 122, 185703 2.5 9

231	Composition and optical properties of dilute-Sb GaN _{1-x} Sb _x highly mismatched alloys grown by MBE. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 465102	3	9
230	Tuning structural, electrical, and optical properties of oxide alloys: ZnO _{1-x} Sex. <i>Journal of Applied Physics</i> , 2012 , 111, 113505	2.5	9
229	Compensation-dependent in-plane magnetization reversal processes in Ga _{1-x} MnxP _{1-y} Sy. <i>Physical Review B</i> , 2008 , 78,	3.3	9
228	Synthesis of highly mismatched alloys using ion implantation and pulsed laser melting. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 261, 1150-1154	1.2	9
227	High dose Cl implantation in ZnSe: Impurity incorporation and radiation damage. <i>Journal of Applied Physics</i> , 1994 , 75, 1378-1383	2.5	9
226	Some aspects of the freely propagating premixed flame in a spatially periodic flow field. <i>Combustion and Flame</i> , 1994 , 97, 375-383	5.3	9
225	Efficient p-type doping of sputter-deposited NiO thin films with Li, Ag, and Cu acceptors. <i>Physical Review Materials</i> , 2020 , 4,	3.2	9
224	Improvement in the electronic quality of pulsed laser deposited CuIn _{0.7} Ga _{0.3} Se ₂ thin films via post-deposition elemental sulfur annealing process. <i>Thin Solid Films</i> , 2016 , 608, 50-56	2.2	9
223	Formation of Nanoscale Composites of Compound Semiconductors Driven by Charge Transfer. <i>Nano Letters</i> , 2016 , 16, 5247-54	11.5	9
222	Exploration of the growth parameter space for MBE-grown GaN _{1-x} B _x highly mismatched alloys. <i>Journal of Crystal Growth</i> , 2015 , 425, 255-257	1.6	8
221	High mobility transparent amorphous CdO-In ₂ O ₃ alloy films synthesized at room temperature. <i>Applied Physics Letters</i> , 2017 , 111, 072108	3.4	8
220	Composition determination of quaternary GaAsPN layers from single X-ray diffraction measurement of quasi-forbidden (002) reflection. <i>Journal of Applied Physics</i> , 2014 , 115, 203102	2.5	8
219	Low cost ion implantation technique. <i>Applied Physics Letters</i> , 2012 , 101, 224104	3.4	8
218	Photovoltaic action from In _x Ga _{1-x} N p-n junctions with x > 0.2 grown on silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2466-2468		8
217	Strain relaxation of CdTe films growing on lattice-mismatched substrates. <i>Applied Physics A: Materials Science and Processing</i> , 2009 , 96, 379-384	2.6	8
216	Preparation of high transmittance ZnO:Al film by pulsed filtered cathodic arc technology and rapid thermal annealing. <i>Applied Surface Science</i> , 2011 , 257, 7019-7022	6.7	8
215	Compensation-dependence of magnetic and electrical properties in Ga _{1-x} MnxP. <i>Applied Physics Letters</i> , 2011 , 98, 012103	3.4	8
214	Synthesis of sub-surface oxide layers by hybrid metal-gas co-implantation into metals. <i>Surface and Coatings Technology</i> , 1998 , 103-104, 293-298	4.4	8

213	InGaN Thin Films Grown by ENABLE and MBE Techniques on Silicon Substrates. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		8
212	Native defects in In _x Ga _{1-x} N alloys. <i>Physica B: Condensed Matter</i> , 2006 , 376-377, 432-435	2.8	8
211	Structure in amorphous semiconductors: Extrinsic and intrinsic. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2005 , 238, 294-301	1.2	8
210	Zinc and phosphorus co-implantation in indium phosphide. <i>Applied Physics Letters</i> , 1998 , 73, 52-54	3.4	8
209	The effects of x-ray induced structural changes on the microstructure of a-Si after thermal crystallization. <i>Applied Physics Letters</i> , 1999 , 75, 2032-2034	3.4	8
208	On the Geometry and Burning Intensity of Bunsen Flames. <i>Combustion Science and Technology</i> , 1994 , 100, 245-270	1.5	8
207	Amphoteric substitutionality and lattice distortion of Ge in InP. <i>Applied Physics Letters</i> , 1994 , 64, 1543-1545	3.4	8
206	Vacuum arc deposition of multilayer X-ray mirrors. <i>Surface and Coatings Technology</i> , 1993 , 61, 257-261	4.4	8
205	The pitting corrosion behavior of aluminum ion implanted with titanium. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1993 , 80-81, 267-270	1.2	8
204	Impurity Gettering by Implanted Carbon in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 147, 97		8
203	The effects of annealing encapsulant and ambient on the barrier height of W _{Nx} /GaAs contact and self-aligned gate field effect transistor fabrication. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1988 , 6, 1779		8
202	ZnO _{1-x} Te _x highly mismatched alloys beyond the dilute alloy limit: Synthesis and electronic band structure. <i>Journal of Applied Physics</i> , 2019 , 125, 155702	2.5	7
201	InGaN pn-junctions grown by PA-MBE: Material characterization and fabrication of nanocolumn electroluminescent devices. <i>Journal of Crystal Growth</i> , 2015 , 425, 393-397	1.6	7
200	Effect of oxygen flow rate on properties of Cu ₄ O ₃ thin films fabricated by radio frequency magnetron sputtering. <i>Journal of Applied Physics</i> , 2020 , 127, 085302	2.5	7
199	Surface hole accumulation and Fermi level stabilization energy in SnTe. <i>Applied Physics Express</i> , 2014 , 7, 091201	2.4	7
198	Evidence of extreme type-III band offset at buried n-type CdO/p-type SnTe interfaces. <i>Physical Review B</i> , 2015 , 91,	3.3	7
197	Facile Synthesis of [Cu(SCH ₃)] Nanowires with High Charge Mobility. <i>ChemPlusChem</i> , 2014 , 79, 559-563	2.8	7
196	Synthesis of Ge _{1-x} Sn _x Alloy Thin Films Using Ion Implantation and Pulsed Laser Melting (II-PLM). <i>Journal of Electronic Materials</i> , 2012 , 41, 837-844	1.9	7

195	Thermal stability of amorphous GaN _{1-x} As _x alloys. <i>Applied Physics Letters</i> , 2011 , 98, 161902	3.4	7
194	GaNAs alloys over the whole composition range grown on crystalline and amorphous substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2503-2505		7
193	Interplay of epitaxial strain and perpendicular magnetic anisotropy in insulating ferromagnetic Ga _{1-x} MnxP _{1-y} Ny. <i>Physical Review B</i> , 2010 , 81,	3.3	7
192	Reversible phase changes in Ge ₂ Au nanoparticles. <i>Applied Physics Letters</i> , 2011 , 98, 193101	3.4	7
191	Irradiation-induced defects in InN and GaN studied with positron annihilation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1087-1090	1.6	7
190	TEM studies of as-grown, irradiated and annealed InN films. <i>Physica B: Condensed Matter</i> , 2007 , 401-402, 646-649	2.8	7
189	Metamorphic InAs _y P _{1-y} (y=0.300.75) and AlIn _{1-x} As _y P _{1-y} buffer layers on InP substrates. <i>Applied Physics Letters</i> , 2007 , 90, 212113	3.4	7
188	Fermi level effects on Mn incorporation in modulation-doped ferromagnetic III _{1-x} MnxV heterostructures. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, S5499-S5508	1.8	7
187	Highly Mismatched Alloys for Intermediate Band Solar Cells. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 865, 571		7
186	Noise reduction in CdZnTe coplanar-grid detectors. <i>IEEE Transactions on Nuclear Science</i> , 2002 , 49, 1950-1953	1.7	7
185	Tribological effects of oxygen ion implantation into stainless steel. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000 , 168, 53-58	1.2	7
184	Polycrystalline hexagonal boron nitride films on SiO ₂ for III _{IV} semiconductor applications. <i>Journal of Materials Research</i> , 1989 , 4, 350-354	2.5	7
183	Plasma Immersion Ion Implantation for Impurity Gettering in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 147, 91		7
182	Effects of oxygen stoichiometry on the phase stability of sputter-deposited CdxZn _{1-x} O alloys. <i>Physical Review Materials</i> , 2019 , 3,	3.2	7
181	Bio-inspired TiO nano-cone antireflection layer for the optical performance improvement of VO thermochromic smart windows. <i>Scientific Reports</i> , 2020 , 10, 11376	4.9	7
180	Morphology and strain control of hierarchical cobalt oxide nanowire electrocatalysts via solvent effect. <i>Nano Research</i> , 2020 , 13, 3130-3136	10	7
179	Effects of doping and rapid thermal processing in Y doped CdO thin films. <i>Journal of Alloys and Compounds</i> , 2019 , 776, 259-265	5.7	7
178	Growth and characterization of Zn _{1-x} Cd _x Te _{1-y} O _y highly mismatched alloys for intermediate band solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 169, 1-7	6.4	6

177	Indium doped Cd _{1-x} Zn _x O alloys as wide window transparent conductors. <i>Thin Solid Films</i> , 2015 , 597, 183-187	2.2	6
176	Electrochemical modification of the optical and electrical properties of Cd-rich Ni Cd _{1-x} alloys. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 147, 127-133	6.4	6
175	Single crystalline In _x Ga _{1-x} N layers on germanium by molecular beam epitaxy. <i>CrystEngComm</i> , 2013 , 15, 9121	3.3	6
174	Heavy p-type doping of ZnSe thin films using Cu ₂ Se in pulsed laser deposition. <i>Applied Physics Letters</i> , 2012 , 101, 042107	3.4	6
173	Local structure of amorphous GaN _{1-x} As _x semiconductor alloys across the composition range. <i>Journal of Applied Physics</i> , 2013 , 113, 243505	2.5	6
172	Self-neutralized ion beam. <i>Journal of Applied Physics</i> , 2011 , 110, 083308	2.5	6
171	Photoluminescence enhancement of Er-doped silica containing Ge nanoclusters. <i>Applied Physics Letters</i> , 2009 , 95, 201904	3.4	6
170	On the electrical conductivity of Ti-implanted alumina. <i>Journal of Applied Physics</i> , 2012 , 111, 063714	2.5	6
169	Interfacial reaction behavior of Pt, Pd, and Ni on ZnSe. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997 , 15, 891		6
168	Direct observation of the amphoteric behavior of Ge in InP modified by P co-implantation. <i>Applied Physics Letters</i> , 1997 , 71, 939-941	3.4	6
167	Experimental and theoretical studies on gadolinium doping in ZnTe. <i>Journal of Applied Physics</i> , 2008 , 103, 023711	2.5	6
166	Oxygen induced band-gap reduction in ZnO _x Se _{1-x} alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 603-606	1.3	6
165	Pressure dependence of optical transitions in semiconducting single-walled carbon nanotubes. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 3367-3373	1.3	6
164	Band anticrossing in highly mismatched group II-VI semiconductor alloys. <i>Journal of Electronic Materials</i> , 2002 , 31, 754-758	1.9	6
163	MOVPE of GaN on sapphire using the alternate precursor 1,1-dimethylhydrazine. <i>Journal of Crystal Growth</i> , 2000 , 221, 246-250	1.6	6
162	Zinc and group V element co-implantation in indium phosphide. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2000 , 168, 65-71	1.2	6
161	Local structural modification in ion damaged InGaAs. <i>Applied Physics Letters</i> , 1996 , 69, 824-826	3.4	6
160	Phase Formation in the Pt/Inp Thin Film System. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 148, 47		6

159	Buoyancy-induced Stokes flow in a wedge-shaped enclosure. <i>Journal of Fluid Mechanics</i> , 1990 , 221, 437-451	3.7	6
158	Near-Infrared-Activated Thermochromic Perovskite Smart Windows.. <i>Advanced Science</i> , 2022 , e2106090	13.6	6
157	Three-dimensional band structure and surface electron accumulation of rs-CdZnO studied by angle-resolved photoemission spectroscopy. <i>Scientific Reports</i> , 2019 , 9, 8026	4.9	5
156	. <i>IEEE Journal of Photovoltaics</i> , 2015 , 5, 878-884	3.7	5
155	Effects of native defects on properties of low temperature grown, non-stoichiometric gallium nitride. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 385101	3	5
154	Realization of rocksalt Zn _{1-x} Cd _x O thin films with an optical band gap above 3.0 eV by molecular beam epitaxy. <i>CrystEngComm</i> , 2020 , 22, 2781-2787	3.3	5
153	Compositional dependence of optical transition energies in highly mismatched Zn _{1-x} Cd _x Te _{1-y} O _y alloys. <i>Applied Physics Express</i> , 2016 , 9, 021202	2.4	5
152	Development of ZnTe-Based Solar Cells. <i>Materials Science Forum</i> , 2013 , 750, 80-83	0.4	5
151	Structural defects and cathodoluminescence of In _x Ga _{1-x} N layers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2248-2250		5
150	N-type doping of InGaN by high energy particle irradiation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1168-1175	1.6	5
149	Effects of Synchrotron X-Rays on PVD Deposited and Ion Implanted Si. <i>Materials Research Society Symposia Proceedings</i> , 1997 , 467, 355		5
148	Copper-doped CdTe films with improved hole mobility. <i>Applied Physics Letters</i> , 2007 , 91, 092113	3.4	5
147	Group III-nitride alloys as photovoltaic materials 2004 ,		5
146	Lattice location of Mn and fundamental Curie temperature limit in ferromagnetic Ga _{1-x} Mn _x As. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004 , 219-220, 636-641	1.2	5
145	Mutual passivation effects in highly mismatched group III-V alloys. <i>IEE Proceedings: Optoelectronics</i> , 2004 , 151, 460-464		5
144	Electron Transport Properties of InN. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 892, 91		5
143	Dielectric mapping of a Pb(Ni _{1/3} Nb _{2/3})O ₃ PbZrO ₃ PbTiO ₃ ternary phase spread. <i>Applied Physics Letters</i> , 2002 , 81, 2062-2064	3.4	5
142	Atomic-level characterisation of the structure of amorphised GaAs utilising EXAFS measurements. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1999 , 147, 148-154	1.2	5

- 141 Amphoteric behavior and precipitation of Ge dopants in InP. *Journal of Applied Physics*, **1996**, 80, 4907-4915 5
- 140 The effect of coimplantation on the electrical activity of implanted carbon in GaAs. *Journal of Applied Physics*, **1993**, 74, 7118-7123 2.5 5
- 139 Fundamental Materials-Issues involved in the Growth of GaN by Molecular Beam Epitaxy. *Materials Research Society Symposia Proceedings*, **1994**, 339, 483 5
- 138 Substitutionality of Te- and Sn-related DX centers in Al_xGa_{1-x}As. *Physical Review B*, **1991**, 43, 2462-2465 3.3 5
- 137 Ion channeling investigation of the lattice location of Sn atoms in GaAs thin films grown by molecular beam epitaxy. *Applied Physics Letters*, **1990**, 56, 1784-1786 3.4 5
- 136 Highly transparent and conducting In doped CdO synthesized by sol-gel solution processing. *Journal of Materials Science*, **2021**, 56, 12607-12619 4.3 5
- 135 Undoped p-type GaN_{1-x}Sbx alloys: Effects of annealing. *Applied Physics Letters*, **2016**, 109, 252102 3.4 5
- 134 Controlling disorder-mediated exchange bias in (Mn,Zn,Fe)₃O₄ thin films. *Journal of Magnetism and Magnetic Materials*, **2016**, 405, 129-136 2.8 4
- 133 Cl-doping effect in ZnTe_{1-x}O_x highly mismatched alloys for intermediate band solar cells. *Journal of Applied Physics*, **2019**, 125, 243109 2.5 4
- 132 Microstructure of GaN_{1-x}Bi_x. *Journal of Electronic Materials*, **2013**, 42, 26-32 1.9 4
- 131 Embedded Binary Eutectic Alloy Nanostructures. *Jom*, **2012**, 64, 1158-1164 2.1 4
- 130 Highly luminescent In_xGa_{1-x}N thin films grown over the entire composition range by energetic neutral atom beam lithography & epitaxy (ENABLE). *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S409-S412 4
- 129 Stacking faults and phase changes in Mg-doped InGaN grown on Si. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2009**, 6, S421-S424 4
- 128 Beta-detected NMR study of the local magnetic field in epitaxial GaAs:Mn. *Physica B: Condensed Matter*, **2009**, 404, 892-895 2.8 4
- 127 Doping of GaN_{1-x}As_x with high As content. *Journal of Applied Physics*, **2011**, 110, 093702 2.5 4
- 126 Characterization of nuclear physics targets using Rutherford backscattering and particle induced X-ray emission. *Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment*, **1997**, 387, 328-332 1.2 4
- 125 Liberation of Ion Implanted Ge Nanocrystals from a Silicon Dioxide Matrix via Hydrofluoric Acid Vapor Etching. *Materials Research Society Symposia Proceedings*, **2003**, 777, 761 4
- 124 Modeling the Stress Evolution of Ion Beam Synthesized Nanocrystals. *Materials Research Society Symposia Proceedings*, **2004**, 821, 252 4

123	Pressure-dependent photoluminescence study of CuGaSe ₂ . <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 3117-3122	1.3	4
122	Structure and low-temperature thermal relaxation of ion-implanted germanium. <i>Journal of Synchrotron Radiation</i> , 2001 , 8, 773-5	2.4	4
121	Evolution of crystallinity of GaN layers grown at low temperature on sapphire with dimethylhydrazine and triethylgallium. <i>Journal of Crystal Growth</i> , 2001 , 231, 89-94	1.6	4
120	High dose uranium ion implantation into silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1988 , 31, 558-562	1.2	4
119	Demonstration of ZnTe _{1-x} O _x Intermediate Band Solar Cell. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 082304	1.4	4
118	Conduction band modifications by d states in vanadium doped CdO. <i>Journal of Alloys and Compounds</i> , 2020 , 822, 153567	5.7	4
117	Controlling the p-Type Conductivity and Composition Range for Bipolar Conduction in Ni _x Cd _{1-x} O Alloys by Acceptor Doping. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 20000-20009	3.8	4
116	Two-Step Chemical Vapor Deposition-Synthesized Lead-Free All-Inorganic CsSbBr Perovskite Microplates for Optoelectronic Applications. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 35930-35940	8.5	4
115	Nitrogen Doping Effect in Cu ₄ O ₃ Thin Films Fabricated by Radio Frequency Magnetron Sputtering. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900363	1.3	4
114	Effective decoupling of seebeck coefficient and the electrical conductivity through isovalent substitution of erbium in bismuth selenide thermoelectric material. <i>Journal of Alloys and Compounds</i> , 2021 , 857, 157559	5.7	4
113	Engineering Electronic Band Structure of Indium-doped Cd _{1-x} Mg _x O Alloys for Solar Power Conversion Applications. <i>Energy Technology</i> , 2018 , 6, 122-126	3.5	4
112	Band alignment of wide bandgap NiO/MoO ₃ and NiO/WO ₃ p-n heterojunctions studied by high-resolution X-ray photoelectron spectroscopy. <i>Journal of Alloys and Compounds</i> , 2021 , 876, 160136	5.7	4
111	Amorphous gallium oxide sulfide: A highly mismatched alloy. <i>Journal of Applied Physics</i> , 2019 , 126, 105708	2.5	3
110	Tellurium n-type doping of highly mismatched amorphous GaN _{1-x} As alloys in plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2014 , 404, 9-13	1.6	3
109	Intermixing studies in GaN _{1-x} Sb _x highly mismatched alloys. <i>Applied Optics</i> , 2017 , 56, B64-B69	0.2	3
108	Determination of N/Ga-rich growth conditions, using in-situ auger electron spectroscopy. <i>Journal of Crystal Growth</i> , 2015 , 425, 2-4	1.6	3
107	Thermal forming of light-weight alloys under a multi-stage forming process. <i>Proceedings of the Institution of Mechanical Engineers, Part C: Journal of Mechanical Engineering Science</i> , 2010 , 224, 797-803	1.3	3
106	Progress on III-nitride/silicon hybrid multijunction solar cells 2010 ,		3

105	InGaN/Si heterojunction tandem solar cells. <i>Conference Record of the IEEE Photovoltaic Specialists Conference, 2008,</i>		3
104	Electronic Band Structure of Highly Mismatched Semiconductor Alloys 2008 , 65-89		3
103	Composition dependence of the hole mobility in GaSb _x As _{1-x} . <i>Applied Physics Letters, 2008</i> , 92, 162105	3.4	3
102	Magnetic anisotropy of ferromagnetic Ga _{1-x} Mn _x As formed by Mn ion implantation and pulsed-laser melting. <i>Journal of Applied Physics, 2008</i> , 104, 043902	2.5	3
101	Mn L _{3,2} X-ray Absorption Spectroscopy And Magnetic Circular Dichroism In Ferromagnetic Ga _{1-x} Mn _x P. <i>AIP Conference Proceedings, 2007</i> ,	0	3
100	Towards identification of localized donor states in InN. <i>Semiconductor Science and Technology, 2007</i> , 22, 1161-1164	1.8	3
99	Synthesis and properties of highly mismatched II-VI alloys. <i>IEE Proceedings: Optoelectronics, 2004</i> , 151, 452-459		3
98	Mutual passivation of group IV donors and isovalent nitrogen in diluted GaN _x As _{1-x} alloys. <i>Physica B: Condensed Matter, 2003</i> , 340-342, 389-393	2.8	3
97	Carrier Concentration Dependencies of Magnetization & Transport in Ga _{1-x} Mn _x As _{1-y} Tey. <i>AIP Conference Proceedings, 2005</i> ,	0	3
96	Group III-nitride Materials for High Efficiency Photoelectrochemical Cells. <i>Materials Research Society Symposia Proceedings, 2005</i> , 884, 1		3
95	Implantation-induced disorder in amorphous Ge: Production and relaxation. <i>Nuclear Instruments & Methods in Physics Research B, 2001</i> , 175-177, 21-25	1.2	3
94	Metal ion mixing in diamond. <i>Surface and Coatings Technology, 2000</i> , 128-129, 375-380	4.4	3
93	Atomic-level characterisation of ion-induced amorphisation in compound semiconductors. <i>Nuclear Instruments & Methods in Physics Research B, 1999</i> , 148, 391-395	1.2	3
92	Direct measurement of CAs in group III+C coimplanted GaAs. <i>Journal of Applied Physics, 1994</i> , 75, 3829-3834	3.4	3
91	Plasma Synthesis of Rare Earth Doped Integrated Optical Waveguides. <i>Materials Research Society Symposia Proceedings, 1995</i> , 392, 241		3
90	The Effect of Co-Implantation on the Electrical Activity of Implanted Carbon in GaAs. <i>Materials Research Society Symposia Proceedings, 1991</i> , 240, 811		3
89	. <i>IEEE Transactions on Magnetics, 1989</i> , 25, 961-964	2	3
88	On-wire axial perovskite heterostructures for monolithic dual-wavelength laser. <i>Nano Energy, 2022</i> , 92, 106778	17.1	3

87	Thermochromic Smart Windows: Organic Hybrid Perovskite (MAPbI ₃ Cl _x) for Thermochromic Smart Window with Strong Optical Regulation Ability, Low Transition Temperature, and Narrow Hysteresis Width (Adv. Funct. Mater. 26/2021). <i>Advanced Functional Materials</i> , 2021 , 31, 2170186	15.6	3
86	Semiempirical modeling of a three sublayer photoanode for highly efficient photoelectrochemical water splitting: Parameter and electrolyte optimizations. <i>Solar Energy Materials and Solar Cells</i> , 2016 , 157, 190-199	6.4	3
85	Mg induced compositional change in InGaN alloys. <i>Semiconductor Science and Technology</i> , 2019 , 34, 025018	1.8	3
84	Potential building energy savings by passive strategies combining daytime radiative coolers and thermochromic smart windows. <i>Case Studies in Thermal Engineering</i> , 2021 , 28, 101517	5.6	3
83	Energy consumption modelling of a passive hybrid system for office buildings in different climates. <i>Energy</i> , 2022 , 239, 121914	7.9	3
82	Effects of the host conduction band energy on the electronic band structure of ZnCdTeO dilute oxide alloys. <i>Journal of Applied Physics</i> , 2019 , 126, 083106	2.5	2
81	Improved ion implant fluence uniformity in hydrogen enhanced glow discharge plasma immersion ion implantation into silicon. <i>Review of Scientific Instruments</i> , 2014 , 85, 063506	1.7	2
80	Structural, magnetic, and transport properties of laser-annealed GaAs:Mn. <i>Journal of Applied Physics</i> , 2009 , 106, 013904	2.5	2
79	Properties of native point defects in In _{1-x} Al _x N alloys. <i>Journal Physics D: Applied Physics</i> , 2009 , 42, 0954063		2
78	Hall mobilities in GaN _x As _{1-x} . <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 1890-1893		2
77	The effects of synchrotron x-rays on the local structure and the recrystallization of ion damaged Si. <i>Semiconductor Science and Technology</i> , 1997 , 12, 460-463	1.8	2
76	High efficiency InAlN-based solar cells. <i>Conference Record of the IEEE Photovoltaic Specialists Conference</i> , 2008 ,		2
75	Characterization of MG-doped InGaN and InAlN alloys grown by MBE for solar applications. <i>Conference Record of the IEEE Photovoltaic Specialists Conference</i> , 2008 ,		2
74	Evidence for p-type InN. <i>AIP Conference Proceedings</i> , 2007 ,	0	2
73	Valence band anticrossing in mismatched III-V semiconductor alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 1711-1714		2
72	Surface studies of semiconducting glass using ion beam methods. <i>Journal of Non-Crystalline Solids</i> , 2000 , 263-264, 416-421	3.9	2
71	Local structures of Ga atoms in amorphous silicon and hydrogenated amorphous silicon before and after synchrotron x-ray irradiation. <i>Applied Physics Letters</i> , 1999 , 75, 3282-3284	3.4	2
70	Electrical activation and local structure of Se atoms in ion-implanted indium phosphide. <i>Journal of Applied Physics</i> , 1996 , 79, 8445-8450	2.5	2

69	Defect-Minimized SiGe Layer Using Ion Beam Synthesis. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 279, 249		2
68	Formation of Buried Iridium Silicide Layer in Silicon by High Dose Iridium Ion Implantation. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 147, 229		2
67	Improved photovoltaic properties of ZnTeO-based intermediate band solar cells 2018 ,		2
66	Temperature-dependent growth of hexagonal and monoclinic gallium sulfide films by pulsed-laser deposition. <i>AIP Advances</i> , 2020 , 10, 105215	1.5	2
65	Structural, optical, and electrical properties of WZ- and RS-ZnCdO thin films on MgO (100) substrate by molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2021 , 867, 159033	5.7	2
64	Effect of Nitrogen Doping on Structural, Electrical, and Optical Properties of CuO Thin Films Synthesized by Radio Frequency Magnetron Sputtering for Photovoltaic Application. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 065019	2	2
63	Optoelectronic properties and doping of magnetron sputtered highly mismatched ZnO _{1-x} Te _x alloy thin films. <i>Journal of Alloys and Compounds</i> , 2021 , 852, 156950	5.7	2
62	Mechanism of non-catalytic chemical vapor deposition growth of all-inorganic CsPbX ₃ (X = Br, Cl) nanowires. <i>Journal of Materials Chemistry C</i> , 2021 , 9, 3229-3238	7.1	2
61	Oxygen vibrational modes in ZnS _{1-x} O _x alloys. <i>Journal of Applied Physics</i> , 2018 , 123, 161537	2.5	2
60	Synthesis of New Nitride Alloys with Mg by Plasma-Assisted Molecular Beam Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 2000122	1.3	1
59	On the Use of Transparent Conductive Oxides in High Concentrator III-V Multijunction Solar Cells 2017 ,		1
58	Growth and characterization of highly mismatched Zn _{1-x} Cd _x Te _{1-y} O _y alloys for intermediate band solar cells 2015 ,		1
57	Planar defects in thin films of InGaN. <i>Microscopy and Microanalysis</i> , 2012 , 18, 1486-1487	0.5	1
56	Microstructure of Mg doped GaNAs alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 453-456		1
55	Band Gap Variation of CdInSe and CdZnS Fabricated by High Throughput Combinatorial Growth Technique 2011 ,		1
54	Wurtzite-to Amorphous-to Cubic Phase Transition of GaN _{1-x} As _x Alloys with Increasing as Content. <i>Solid State Phenomena</i> , 2012 , 186, 74-77	0.4	1
53	Band structure engineering of ZnO 1-x Se x alloys 2010 ,		1
52	Chapter 3 Fermi Level Effects on Mn Incorporation in III-Mn-V Ferromagnetic Semiconductors. <i>Semiconductors and Semimetals</i> , 2008 , 82, 89-133	0.6	1

51	EXAFS measurements of metal-decorated nanocavities in Si. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2003 , 199, 179-184	1.2	1
50	Direct observation of structural relaxation in amorphous compound semiconductors. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2003 , 206, 1024-1027	1.2	1
49	Electronic and Optical Properties of Energetic Particle-Irradiated In-rich InGaN. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 864, 7101		1
48	Structural characterisation of amorphised compound semiconductors. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2001 , 175-177, 280-285	1.2	1
47	Ion-implanted charge collection contacts for high purity silicon detectors operated at 20 mK. <i>Review of Scientific Instruments</i> , 1995 , 66, 2625-2630	1.7	1
46	EXAFS Analysis of Dilute Magnetic Semiconductor thin Films Synthesized by the Ion Beam Technique. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 307, 179		1
45	An Investigation on the Lattice Site Location of the Excess Arsenic Atoms in GaAs layers Grown by Low Temperature Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 241, 145		1
44	Analysis of pseudomorphic GaAs/InGaAs/AlGaAs modulation-doped field-effect transistor structures by secondary-ion mass spectrometry and ion channeling. <i>Applied Physics Letters</i> , 1991 , 58, 1305-1307	3.4	1
43	Low Energy Ion Beam Modification of AlN _x O _y Thin Film for Insulated Gate Field Effect Transistors. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 268, 377		1
42	Ion Beam Modification of the Y-Ba-Cu-O System with the Mevva High Current Metal Ion Source. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 147, 391		1
41	Investigation of the Interface Integrity of the Thermally Stable Wn/GaAs Schottky Contacts. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 148, 41		1
40	Plasma Immersion Surface Modification With Metal Ion Plasma. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 223, 371		1
39	Doping limitation due to self-compensation by native defects in In-doped rocksalt CdZnO. <i>Journal of Physics Condensed Matter</i> , 2021 , 34,	1.8	1
38	Effects of Al doping on the structural, electrical, and optical properties of rock-salt ZnCdO thin films grown by molecular beam epitaxy. <i>Journal of Physics and Chemistry of Solids</i> , 2022 , 163, 110571	3.9	1
37	Improved two-step photon absorption current by Cl-doping in ZnTeO-based intermediate band solar cells with n-ZnS layer. <i>Solar Energy Materials and Solar Cells</i> , 2022 , 235, 111456	6.4	1
36	Electronic structure and properties of Cu _{2-x} S thin films: Dependence of phase structures and free-hole concentrations. <i>Applied Surface Science</i> , 2022 , 572, 151530	6.7	1
35	Electrical activity and precipitation behavior of copper in gallium arsenide 1995 , 61, 7		1
34	THz transient photoconductivity of the III ^V dilute nitride GaP _{1-y} As _y N _x . <i>Semiconductor Science and Technology</i> , 2018 , 33, 125009	1.8	1

33	Flexibility of Room-Temperature-Synthesized Amorphous CdO-InO Alloy Films and Their Application as Transparent Conductors in Solar Cells. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 43795-43805	9.5	1
32	Electrical conductivity and effects of mechanical bending of flexible amorphous transparent conducting CdO-Ga ₂ O ₃ films synthesized by room temperature sputtering. <i>Journal of Alloys and Compounds</i> , 2021 , 875, 160000	5.7	1
31	Effects of free carriers on the optical properties of high mobility transition metal doped In ₂ O ₃ transparent conductors. <i>Physical Review Materials</i> , 2021 , 5,	3.2	1
30	Reversible photochromic and photoluminescence in iodide perovskites. <i>Thin Solid Films</i> , 2021 , 737, 138950	5.0	1
29	Effects of acceptor doping and oxygen stoichiometry on the properties of sputter-deposited p-type rocksalt Ni Zn ₁₀ (0.3-1.0) alloys. <i>Journal of Alloys and Compounds</i> , 2022 , 905, 164224	5.7	1
28	Improving the p-type conductivity of Cu ₂ O thin films by Ni doping and their heterojunction with n-ZnO. <i>Applied Surface Science</i> , 2022 , 590, 153047	6.7	1
27	Amorphous CdO-In ₂ O ₃ Electrode for Perovskite-Based Bifacial and Tandem Photovoltaic Technologies with High Energy Production. <i>Solar Rrl</i> , 2100809	7.1	0
26	Amorphous CdO-In ₂ O ₃ alloy thin films with high conductivity and transparency synthesized by sol-gel method. <i>Journal of Alloys and Compounds</i> , 2022 , 893, 162341	5.7	0
25	Electronically Controlled Chemical Stability of Compound Semiconductor Surfaces. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 32543-32551	9.5	
24	Surface modification of NiCdO barrier layer in complex photoanodes and TiO ₂ protective coating for efficient and stable water dissociation. <i>Journal of Solid State Electrochemistry</i> , 2017 , 21, 803-812	2.6	
23	Fabrication and characterization of multiband solar cells based on highly mismatched alloys. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012067	0.3	
22	Structural studies of GaN _{1-x} As _x and GaN _{1-x} Bi _x alloys for solar cell applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1586-1589		
21	MBE GROWTH AND CHARACTERIZATION OF Mg-DOPED III-NITRIDES ON SAPPHIRE. <i>Selected Topics in Electronics and Systems</i> , 2009 , 113-119	0	
20	MBE GROWTH AND CHARACTERIZATION OF Mg-DOPED III-NITRIDES ON SAPPHIRE. <i>International Journal of High Speed Electronics and Systems</i> , 2009 , 19, 113-119	0.5	
19	Growth by Molecular Beam Epitaxy of GaNAs Alloys with High As Content for Potential Photoanode Applications in Hydrogen Production. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1167, 7		
18	Optical properties of ion beam synthesized nitrogen-rich GaN _{1-x} As _x . <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S796-S799		
17	Compositional Ordering in In _x Ga _{1-x} N and its influence on optical properties. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 831, 126		
16	A Chemical Approach to 3-D Lithographic Patterning of Si and Ge Nanocrystals. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 901, 1		

- 15 Germanium Nanocrystals Embedded in Sapphire. *Materials Research Society Symposia Proceedings*, **2005**, 880, 1
- 14 Mutual Passivation in Dilute GaN_xAs_{1-x} Alloys. *Materials Research Society Symposia Proceedings*, **2005**, 864, 811
- 13 Effects of structural defects on the activation of sulfur donors in GaN_xAs_{1-x} formed by N implantation. *Physica B: Condensed Matter*, **2001**, 308-310, 874-876 2.8
- 12 Arsenic Incorporation in Gallium Nitride grown by Metalorganic Chemical Vapor Deposition using Dimethylhydrazine and Tertiarybutylarsenic. *Materials Research Society Symposia Proceedings*, **2000**, 622, 6111
- 11 Synthesis of III-N_x-V_{1-x} Thin Films by N Ion Implantation. *Materials Research Society Symposia Proceedings*, **2000**, 650, 1331
- 10 synthesis of III-N_x-V_{1-x} Thin Films by N Ion Implantation. *Materials Research Society Symposia Proceedings*, **2000**, 647, 1
- 9 Local Structural Changes of Ion Damaged InGaAs. *Materials Research Society Symposia Proceedings*, **1998**, 540, 79
- 8 Reducing Dislocation Density by Sequential Implantation of Ge and C in Si. *Materials Research Society Symposia Proceedings*, **1993**, 298, 139
- 7 The Effects of Amorphous Layer Regrowth on Carbon Activation in GaAs and InP. *Materials Research Society Symposia Proceedings*, **1993**, 316, 325
- 6 Photoluminescence Spectroscopy and Rutherford Backscattering Channeling Evaluation of Various Capping Techniques for Rapid Thermal Annealing of Ion-Implanted ZnSe. *Materials Research Society Symposia Proceedings*, **1994**, 340, 549
- 5 Tem Structure Investigations of Low-Temperature MBE Grown InAlAs Layers on INP Substrate. *Materials Research Society Symposia Proceedings*, **1992**, 263, 347
- 4 Thin Film Reactions on Alloy Semiconductor Substrates. *Materials Research Society Symposia Proceedings*, **1990**, 202, 713
- 3 Properties of Cu in GaAs. *Materials Research Society Symposia Proceedings*, **1990**, 209, 379
- 2 Energetic Beam Synthesis of Dilute Nitrides and Related Alloys **2008**, 1-34
- 1 Controlling electrical and optical properties of wurtzite Cd_xZn_{1-x}O with high Cd contents via native defects manipulation by low-temperature annealing. *Journal of Applied Physics*, **2022**, 131, 175104²⁻⁵